

Features

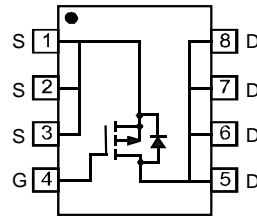
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)



Top View



Top View
Internal Schematic

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 25	V
Continuous Drain Current (Note 3)	Steady State ($V_{GS} = -4.5$)	$T_A = 25^\circ\text{C}$	I_D	-7.3	A
		$T_A = 85^\circ\text{C}$		-4.7	A
Pulsed Drain Current (Note 4)			I_{DM}	-80	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	1.3	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	96.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on 1in. x 1in. FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.
 4. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} = 0V, I _D = -1mA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	-1.7	-2.5	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	13	16	mΩ	V _{GS} = -20V, I _D = -11A
			15	20		V _{GS} = -10V, I _D = -10A
			21	29		V _{GS} = -5V, I _D = -5A
Forward Transfer Admittance	Y _{fs}	-	22	-	S	V _{DS} = -5V, I _D = -10A
Diode Forward Voltage	V _{SD}	-	-0.74	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	-	1614	-	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	226	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	214	-	pF	
Gate Resistance	R _g	-	6.8	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge at 10V	Q _g	-	35.4	-	nC	V _{GS} = -10V, V _{DS} = -15V, I _D = -10A
Total Gate Charge at 5V	Q _g	-	18.9	-	nC	
Gate-Source Charge	Q _{gs}	-	4.6	-	nC	V _{GS} = -5V, V _{DS} = -15V, I _D = -10A
Gate-Drain Charge	Q _{gd}	-	5.7	-	nC	
Turn-On Delay Time	t _{D(on)}	-	8.6	-	ns	V _{DS} = -15V, V _{GS} = -10V, R _L = 1.5Ω, R _{GEN} = 3Ω,
Turn-On Rise Time	t _r	-	12.7	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	44.9	-	ns	
Turn-Off Fall Time	t _f	-	22.8	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.
6. Guaranteed by design. Not subject to production testing.

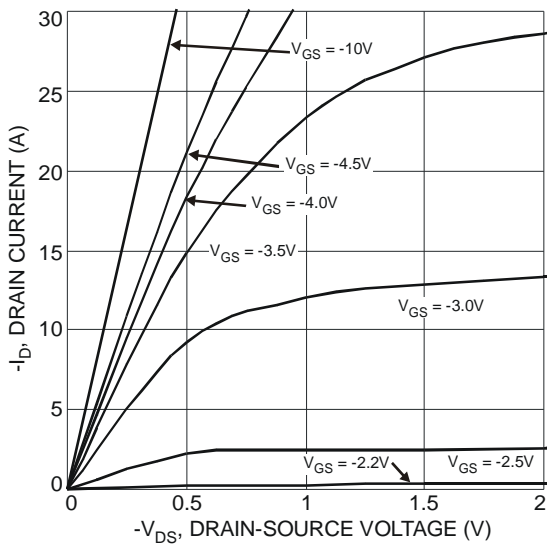


Fig. 1 Typical Output Characteristic

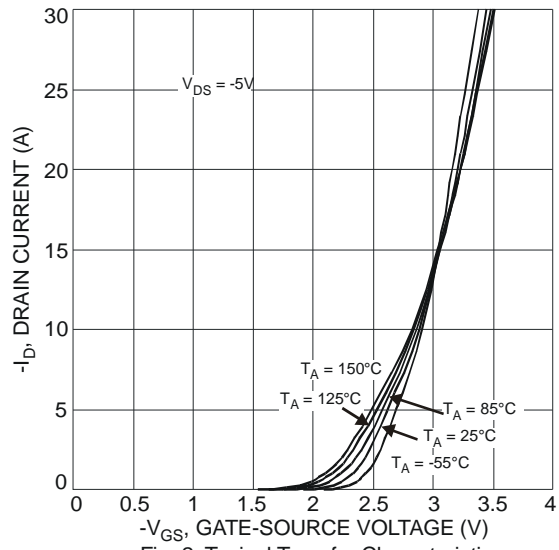


Fig. 2 Typical Transfer Characteristic

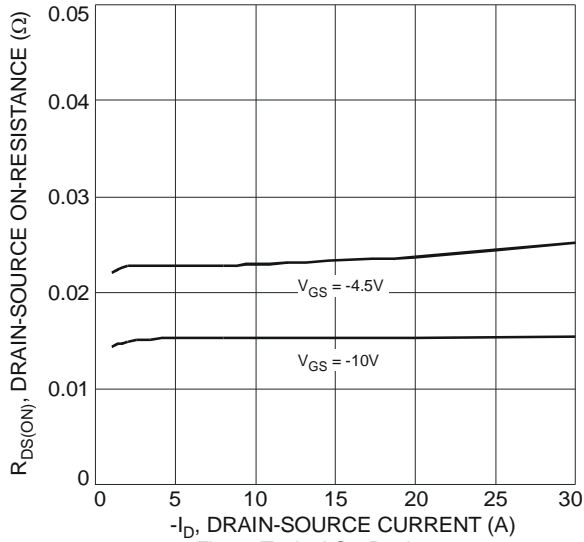


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

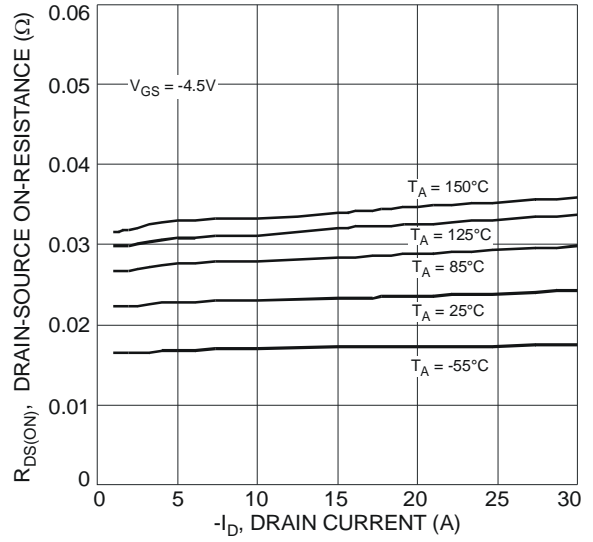


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

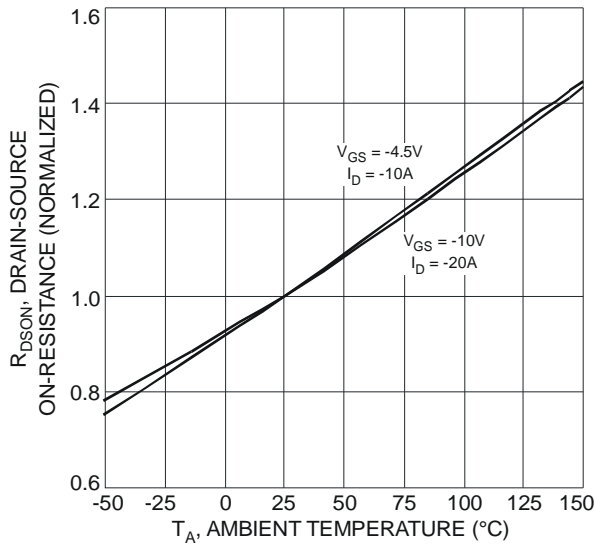


Fig. 5 On-Resistance Variation with Temperature

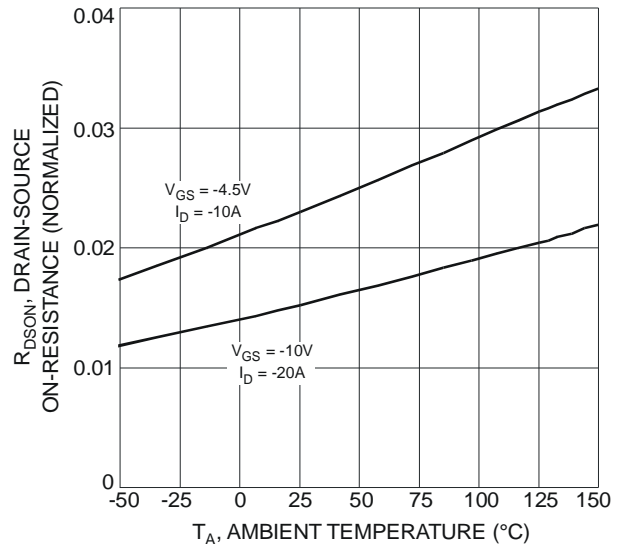


Fig. 6 On-Resistance Variation with Temperature

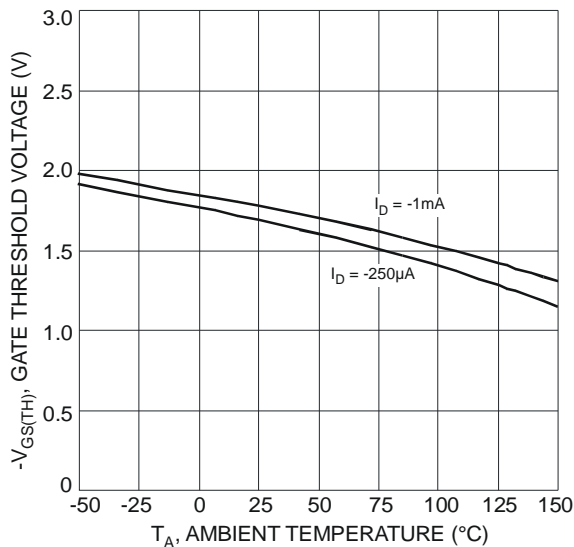


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

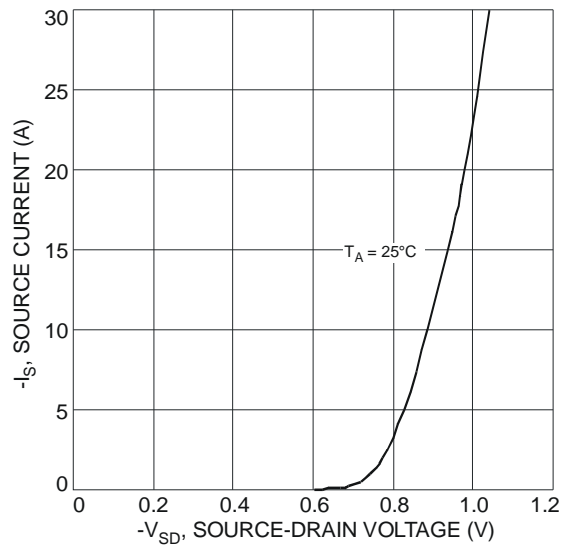


Fig. 8 Diode Forward Voltage vs. Current

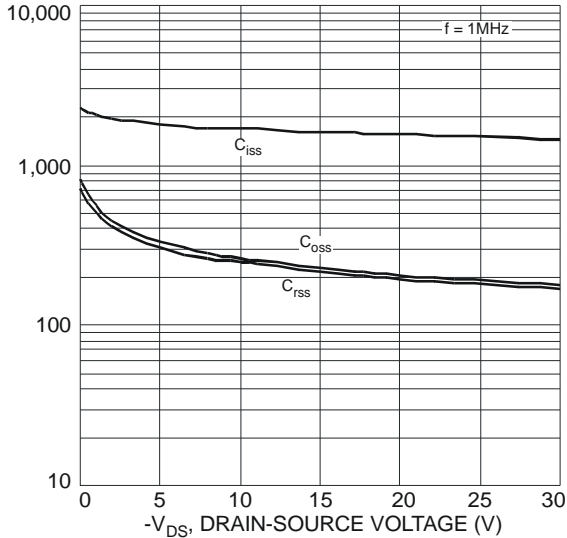


Fig. 9 Typical Total Capacitance

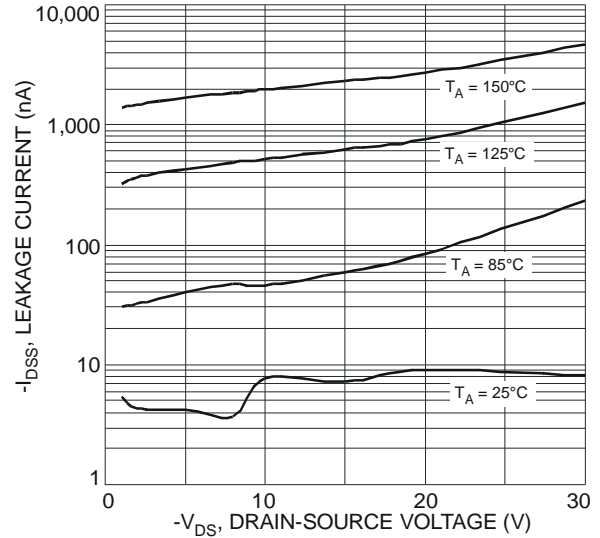


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

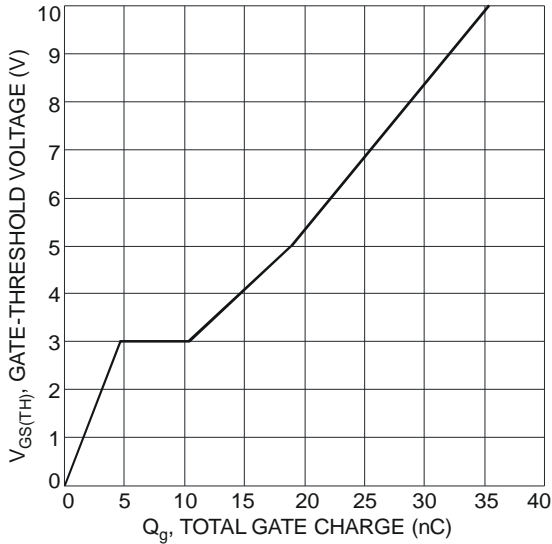


Fig. 11 Gate Threshold Voltage vs. Total Gate Charge

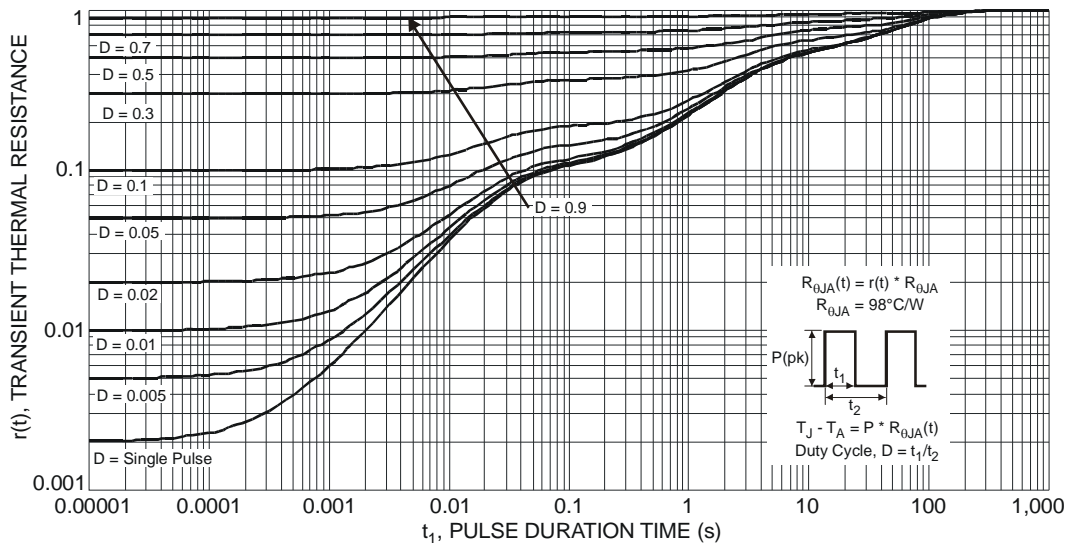


Fig. 12 Transient Thermal Response

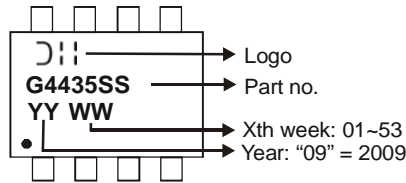
NEW PRODUCT

Ordering Information (Note 7)

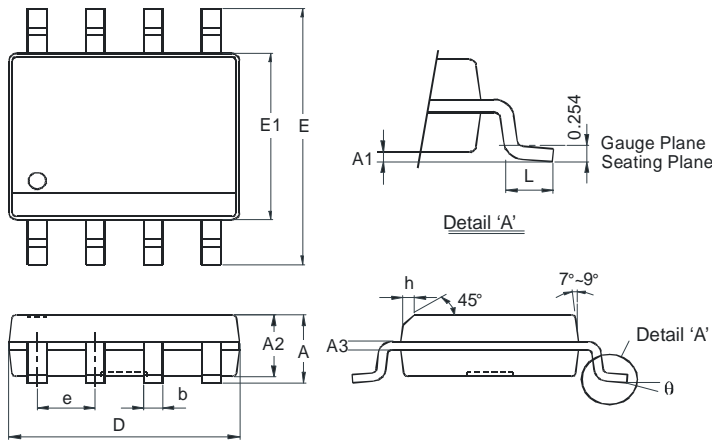
Part Number	Case	Packaging
DMG4435SSS-13	SO-8	2500 / Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

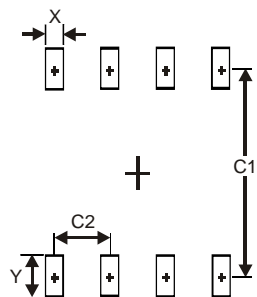


Package Outline Dimensions



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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